

XPT IGBT

$$V_{CES} = 1200V$$

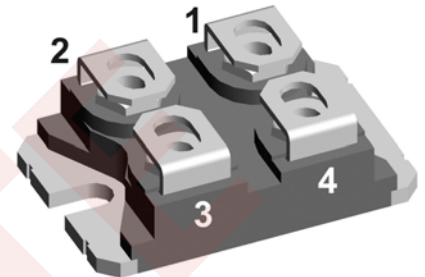
$$I_{C25} = 88A$$

$$V_{CE(sat)} = 1.8V$$

Copack

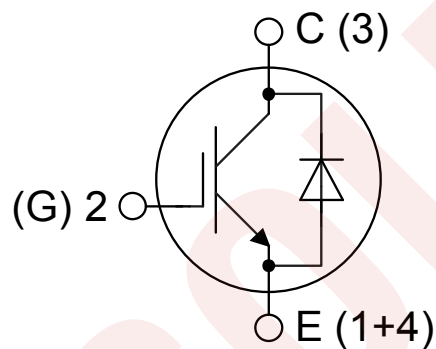
Part number

IXA60IF1200NA



Backside: isolated

E72873

**Features / Advantages:**

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - low EMI
 - square RBSOA @ 3x I_C
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Applications:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies
- Inductive heating, cookers
- Pumps, Fans

Package: SOT-227B (minibloc)

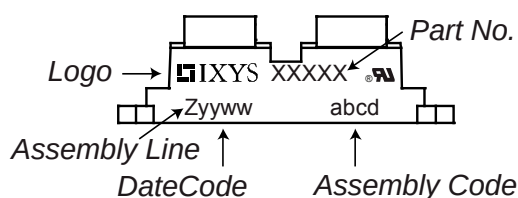
- Isolation Voltage: 3000 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Base plate: Copper internally DCB isolated
- Advanced power cycling
- Either emitter terminal can be used as main or Kelvin emitter

IGBT				Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
V _{CES}	collector emitter voltage	T _{VJ} = 25°C			1200	V	
V _{GES}	max. DC gate voltage				±20	V	
V _{GEM}	max. transient gate emitter voltage				±30	V	
I _{C25}	collector current	T _C = 25°C			88	A	
I _{C80}		T _C = 80°C			56	A	
P _{tot}	total power dissipation	T _C = 25°C			290	W	
V _{CE(sat)}	collector emitter saturation voltage	I _C = 50A; V _{GE} = 15 V		1.8	2.1	V	
		T _{VJ} = 25°C		2.1		V	
		T _{VJ} = 125°C				V	
V _{GE(th)}	gate emitter threshold voltage	I _C = 2mA; V _{GE} = V _{CE}	5.4	5.9	6.5	V	
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V			0.1	mA	
		T _{VJ} = 25°C				mA	
		T _{VJ} = 125°C		0.1		mA	
I _{GES}	gate emitter leakage current	V _{GE} = ±20 V			500	nA	
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 50 A		190		nC	
t _{d(on)}	turn-on delay time	inductive load V _{CE} = 600V; I _C = 50 A V _{GE} = ±15 V; R _G = 15 Ω	T _{VJ} = 125°C	70		ns	
t _r	current rise time			40		ns	
t _{d(off)}	turn-off delay time			250		ns	
t _f	current fall time			100		ns	
E _{on}	turn-on energy per pulse			4.5		mJ	
E _{off}	turn-off energy per pulse			5.5		mJ	
RBSOA	reverse bias safe operating area	V _{GE} = ±15 V; R _G = 15 Ω					
I _{CM}		V _{CEmax} = 1200V			150	A	
SCSOA	short circuit safe operating area	V _{CEmax} = 1200 V					
t _{sc}	short circuit duration	V _{CE} = 900 V; V _{GE} = ±15 V			10	μs	
I _{sc}	short circuit current	R _G = 15 Ω; non-repetitive		200		A	
R _{thJC}	thermal resistance junction to case				0.43	K/W	
R _{thCH}	thermal resistance case to heatsink			0.10		K/W	
Diode							
V _{RRM}	max. repetitive reverse voltage	T _{VJ} = 25°C			1200	V	
I _{F25}	forward current	T _C = 25°C			85	A	
I _{F80}		T _C = 80°C			51	A	
V _F	forward voltage	I _F = 60A			2.20	V	
		T _{VJ} = 25°C		1.95		V	
		T _{VJ} = 125°C				V	
I _R	reverse current	V _R = V _{RRM}			*	mA	
	* not applicable, see Ices at IGBT			*		mA	
Q _{rr}	reverse recovery charge	V _R = 600 V -di _F /dt = E+03 A/μs I _F = 60A; V _{GE} = 0 V	T _{VJ} = 125°C	8		μC	
I _{RM}	max. reverse recovery current			60		A	
t _{rr}	reverse recovery time			350		ns	
E _{rec}	reverse recovery energy			2.5		mJ	
R _{thJC}	thermal resistance junction to case				0.6	K/W	
R _{thCH}	thermal resistance case to heatsink			0.10		K/W	

Package SOT-227B (minibloc)				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal ¹⁾				150	A
T_{VJ}	virtual junction temperature			-40		150	°C
T_{op}	operation temperature			-40		125	°C
T_{stg}	storage temperature			-40		150	°C
Weight					30		g
M_D	mounting torque			1.1		1.5	Nm
M_T	terminal torque			1.1		1.5	Nm
$d_{Spp/App}$	creepage distance on surface striking distance through air	terminal to terminal	10.5	3.2			mm
$d_{Spb/Apb}$		terminal to backside	8.6	6.8			mm
V_{ISOL}	isolation voltage	$t = 1 \text{ second}$		3000			V
		$t = 1 \text{ minute}$	50/60 Hz, RMS; $I_{ISOL} \leq 1 \text{ mA}$	2500			V

¹⁾ I_{RMS} is typically limited by the pin-to-chip resistance (1); or by the current capability of the chip (2). In case of (1) and a product with multiple pins for one chip-potential, the current capability can be increased by connecting the pins as one contact.

Product Marking



Part description

I = IGBT
 X = XPT IGBT
 A = Gen 1 / std
 60 = Current Rating [A]
 IF = Copack
 1200 = Reverse Voltage [V]
 NA = SOT-227B (minibloc)

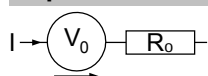
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	IXA60IF1200NA	IXA60IF1200NA	Tube	10	508765

Similar Part	Package	Voltage class
IXA70I1200NA	SOT-227B (minibloc)	1200

Equivalent Circuits for Simulation

* on die level

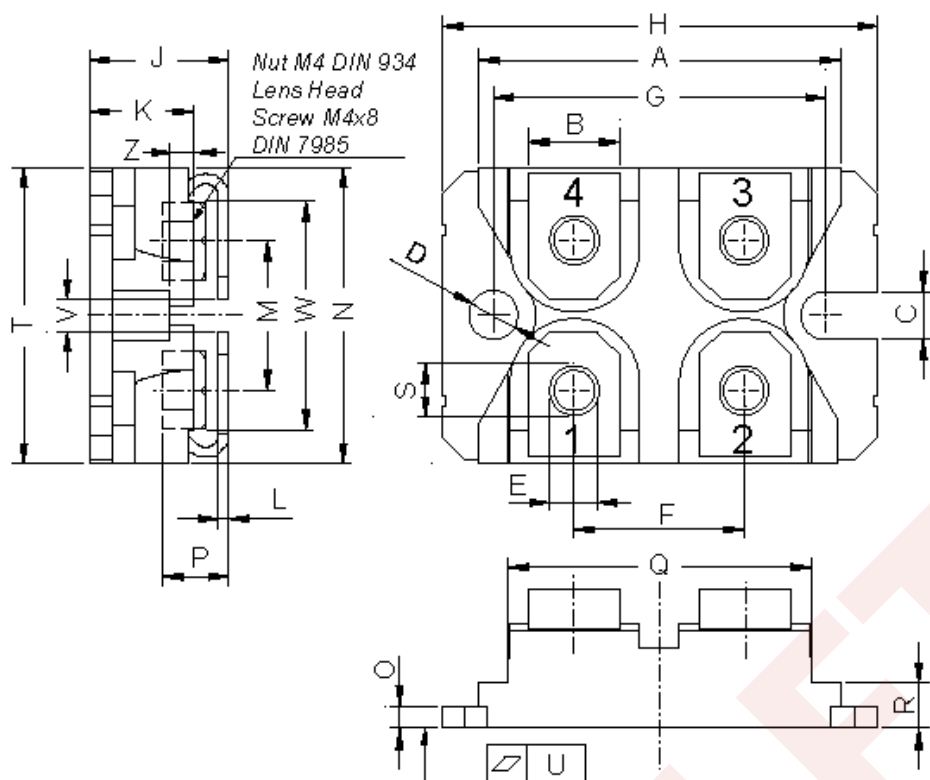
$T_{VJ} = 150^\circ\text{C}$



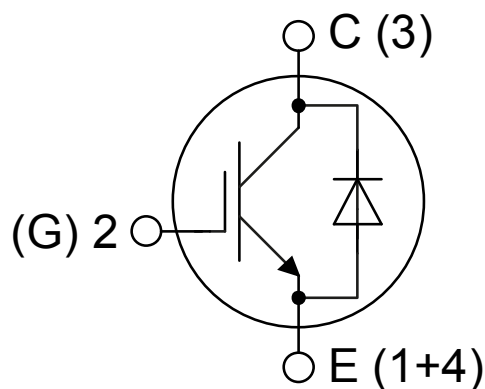
$V_{0 \max}$ threshold voltage
 $R_{0 \max}$ slope resistance *

	IGBT	Diode	
$V_{0 \max}$	1.1	1.25	V
$R_{0 \max}$	28	14.2	mΩ

Outlines SOT-227B (minibloc)



Dim.	Millimeter		Inches	
	min	max	min	max
A	31.50	31.88	1.240	1.255
B	7.80	8.20	0.307	0.323
C	4.09	4.29	0.161	0.169
D	4.09	4.29	0.161	0.169
E	4.09	4.29	0.161	0.169
F	14.91	15.11	0.587	0.595
G	30.12	30.30	1.186	1.193
H	37.80	38.23	1.488	1.505
J	11.68	12.22	0.460	0.481
K	8.92	9.60	0.351	0.378
L	0.74	0.84	0.029	0.033
M	12.50	13.10	0.492	0.516
N	25.15	25.42	0.990	1.001
O	1.95	2.13	0.077	0.084
P	4.95	6.20	0.195	0.244
Q	26.54	26.90	1.045	1.059
R	3.94	4.42	0.155	0.167
S	4.55	4.85	0.179	0.191
T	24.59	25.25	0.968	0.994
U	-0.05	0.10	-0.002	0.004
V	3.20	5.50	0.126	0.217
W	19.81	21.08	0.780	0.830
Z	2.50	2.70	0.098	0.106



IGBT

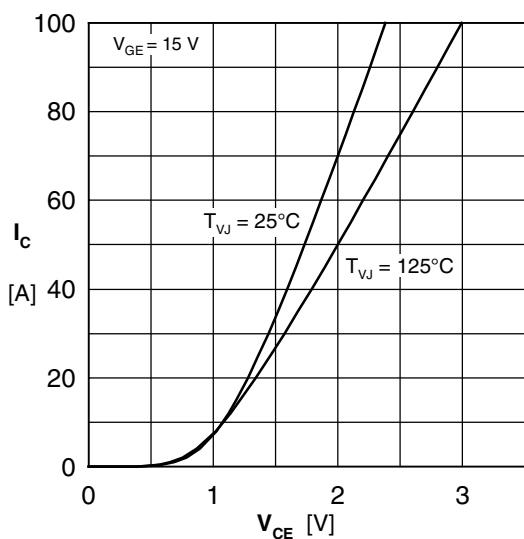


Fig. 1 Typ. output characteristics

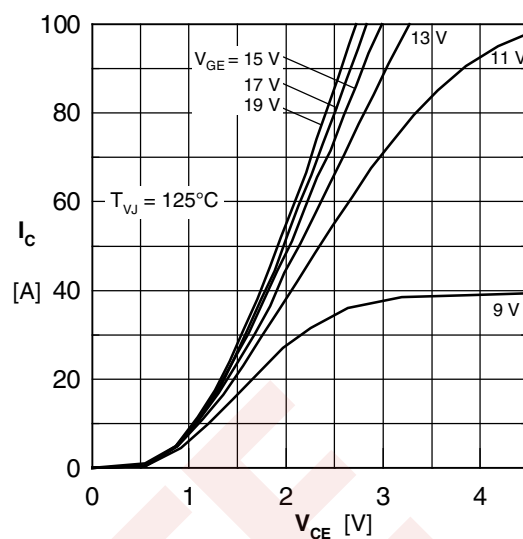


Fig. 2 Typ. output characteristics

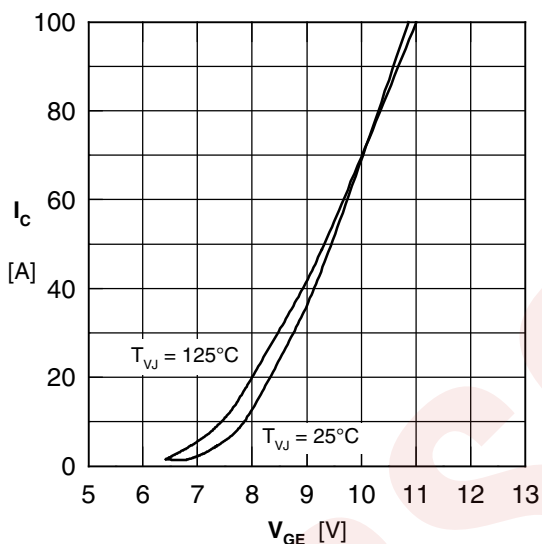


Fig. 3 Typ. transfer characteristics

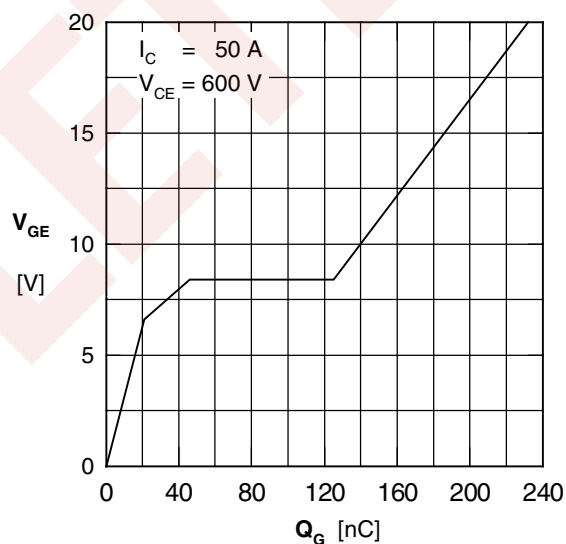


Fig. 4 Typ. turn-on gate charge

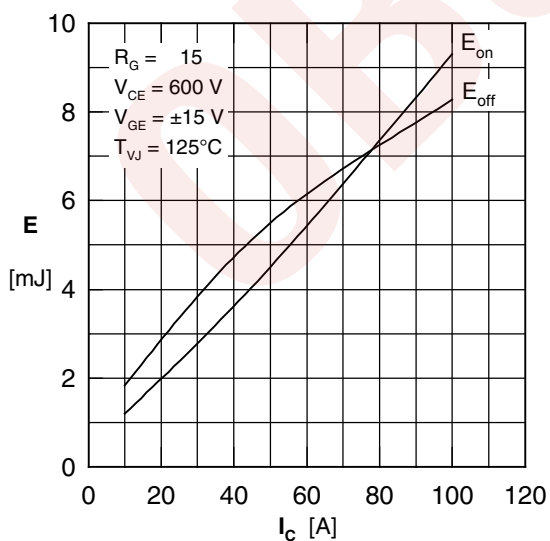


Fig. 5 Typ. switching energy vs. collector current

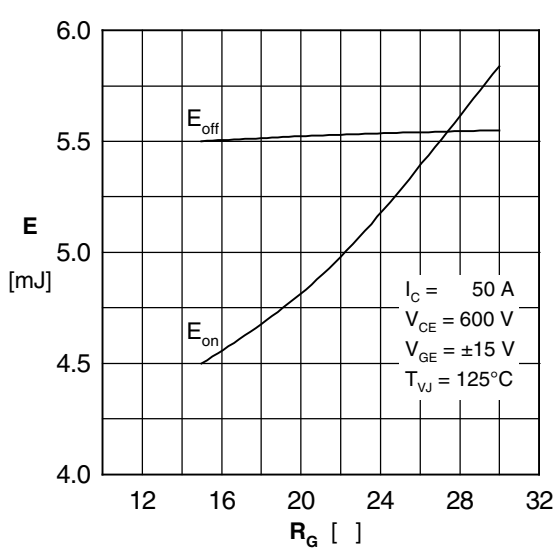


Fig. 6 Typ. switching energy vs. gate resistance

Diode

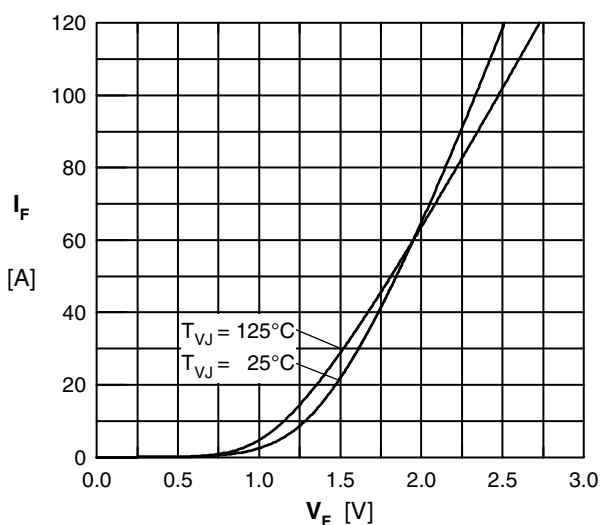
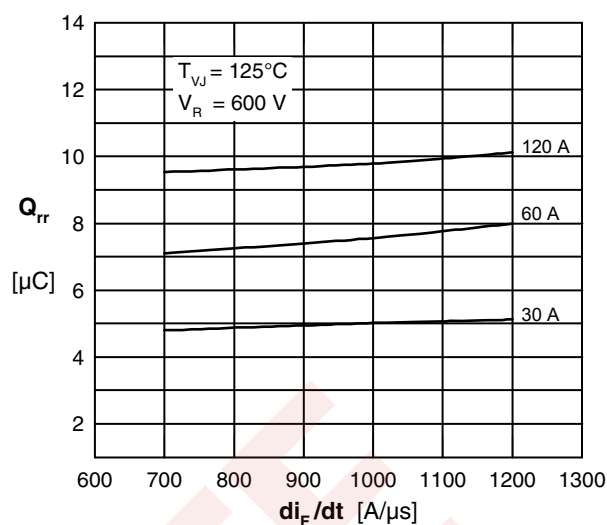
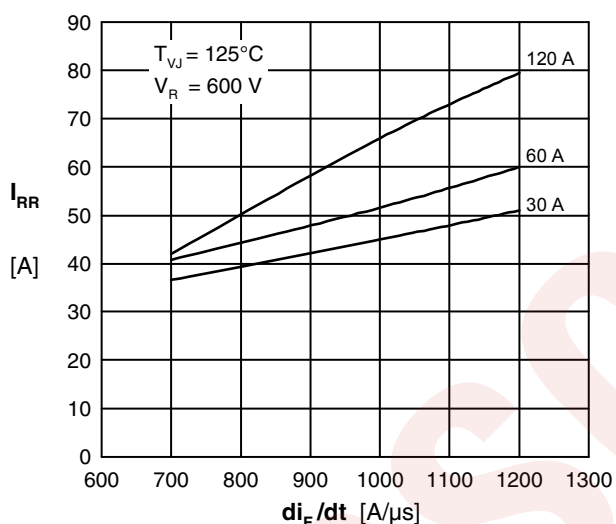
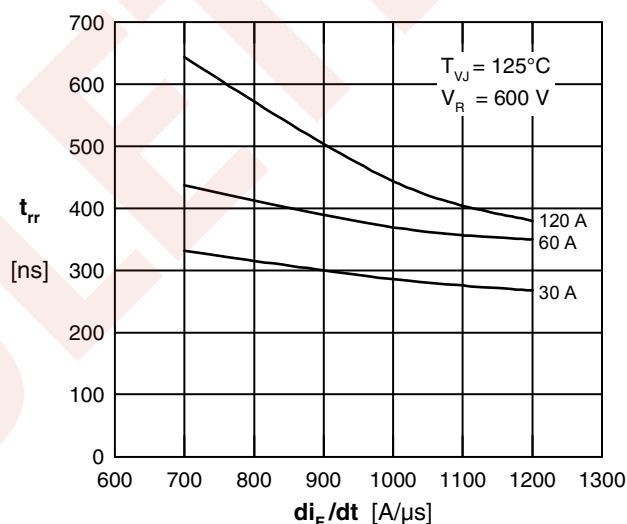
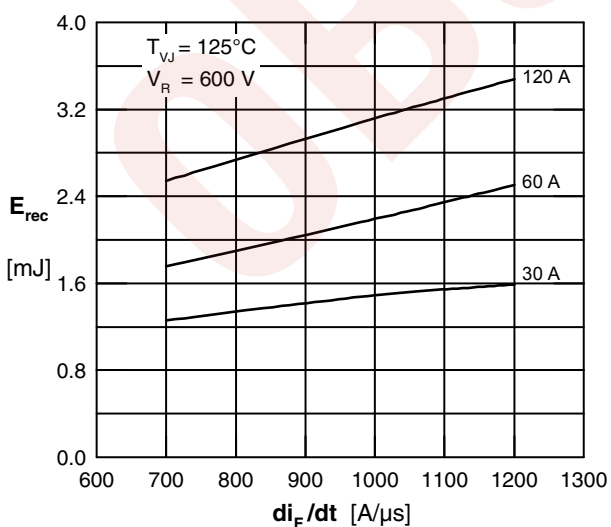
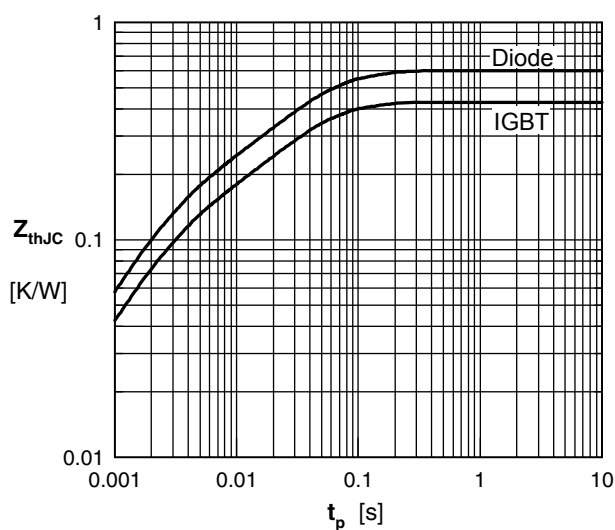
Fig. 7 Typ. Forward current versus V_F Fig. 8 Typ. reverse recov. charge Q_{rr} vs. di/dt Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt Fig. 10 Typ. recovery time t_{rr} versus di/dt Fig. 11 Typ. recovery energy E_{rec} versus di/dt 

Fig. 12 Typ. transient thermal impedance

OBSOLETE

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IXYS
A Littelfuse Technology

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